



Bipolar PNP Bare Die – BTP070

Part Description

The BTP070 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -40V
- VCEO = -35V
- VEBO = -25V
- hFE = 100-400 @ VCE = 0V, IC = -0.012A
- VCE(Sat) = -0.2V @ IC = -0.024A, IB = -1mA
- fT = 30 MHz @ VCE = -6V, IE = 0A
- COBO = 20pF @ VCB = -6V

Features

High VEBO. Designed to provide performance equivalent to CMPT404A

Die Size (Unawn)

800µm X 800µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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